

## NCE N-Channel Enhancement Mode Power MOSFET

### Description

The NCE0224DA uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

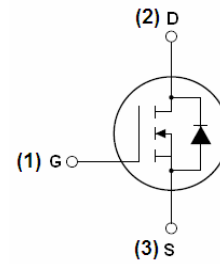
- $V_{DS} = 200V, I_D = 24A$   
 $R_{DS(ON)} < 80m\Omega @ V_{GS} = 10V$  (Typ: 62m $\Omega$ )
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

### Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

**100% UIS TESTED!**

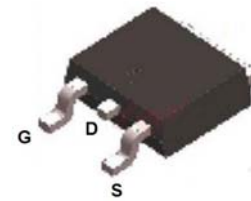
**100%  $\Delta V_{ds}$  TESTED!**



Schematic diagram



Marking and pin assignment



TO-263-2L top view

### Package Marking and Ordering Information

| Device Marking | Device    | Device Package | Reel Size | Tape width | Quantity |
|----------------|-----------|----------------|-----------|------------|----------|
| NCE0224DA      | NCE0224DA | TO-263-2L      | -         | -          | -        |

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

| Parameter   | Symbol             | Limit      | Unit       |
|---|--------------------|------------|------------|
| Drain-Source Voltage                              | $V_{DS}$           | 200        | V          |
| Gate-Source Voltage                               | $V_{GS}$           | $\pm 20$   | V          |
| Drain Current-Continuous                          | $I_D$              | 24         | A          |
| Drain Current-Continuous( $T_C = 100^\circ C$ )   | $I_D(100^\circ C)$ | 17         | A          |
| Pulsed Drain Current                              | $I_{DM}$           | 100        | A          |
| Maximum Power Dissipation                         | $P_D$              | 150        | W          |
| Single pulse avalanche energy <sup>(Note 5)</sup> | $E_{AS}$           | 250        | mJ         |
| Operating Junction and Storage Temperature Range  | $T_J, T_{STG}$     | -55 To 175 | $^\circ C$ |

**Thermal Characteristic**

|  |                 |   |      |
|--|-----------------|---|------|
| Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup> | $R_{\theta JC}$ | 1 | °C/W |
|--|-----------------|---|------|

**Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

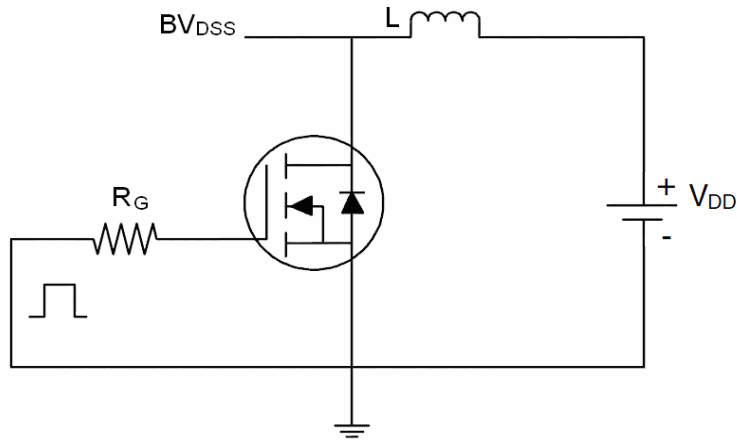
| Parameter  | Symbol       | Condition   | Min | Typ  | Max       | Unit       |
|--|--------------|---|-----|------|-----------|------------|
| <b>Off Characteristics</b>                           |              |   |     |      |           |            |
| Drain-Source Breakdown Voltage                       | $BV_{DSS}$   | $V_{GS}=0V, I_D=250\mu A$   | 200 | 220  | -         | V          |
| Zero Gate Voltage Drain Current                      | $I_{DSS}$    | $V_{DS}=200V, V_{GS}=0V$  | -   | -    | 1         | $\mu A$    |
| Gate-Body Leakage Current                            | $I_{GSS}$    | $V_{GS}=\pm 20V, V_{DS}=0V$   | -   | -    | $\pm 100$ | nA         |
| <b>On Characteristics</b> <sup>(Note 3)</sup>        |              |   |     |      |           |            |
| Gate Threshold Voltage                               | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$   | 1   | 1.5  | 2         | V          |
| Drain-Source On-State Resistance                     | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=15A$   | -   | 62   | 80        | m $\Omega$ |
| Forward Transconductance                             | $g_{FS}$     | $V_{DS}=50V, I_D=15A$   | 30  | -    | -         | S          |
| <b>Dynamic Characteristics</b> <sup>(Note 4)</sup>   |              |   |     |      |           |            |
| Input Capacitance                                    | $C_{iss}$    | $V_{DS}=25V, V_{GS}=0V,$<br>$F=1.0\text{MHz}$   |     | 4200 |           | PF         |
| Output Capacitance                                   | $C_{oss}$    |   |     | 163  |           | PF         |
| Reverse Transfer Capacitance                         | $C_{rss}$    |   |     | 75   |           | PF         |
| <b>Switching Characteristics</b> <sup>(Note 4)</sup> |              |   |     |      |           |            |
| Turn-on Delay Time                                   | $t_{d(on)}$  | $V_{DD}=100V, I_D=15A$<br>$V_{GS}=10V, R_{GEN}=2.5\Omega$                             | -   | 10   | -         | nS         |
| Turn-on Rise Time                                    | $t_r$        |   | -   | 18   | -         | nS         |
| Turn-Off Delay Time                                  | $t_{d(off)}$ |   | -   | 22   | -         | nS         |
| Turn-Off Fall Time                                   | $t_f$        |   | -   | 5    | -         | nS         |
| Total Gate Charge                                    | $Q_g$        | $V_{DS}=100V, I_D=15A,$<br>$V_{GS}=10V$   |     | 60   |           | nC         |
| Gate-Source Charge                                   | $Q_{gs}$     |   |     | 19   |           | nC         |
| Gate-Drain Charge                                    | $Q_{gd}$     |   |     | 17   |           | nC         |
| <b>Drain-Source Diode Characteristics</b>            |              |   |     |      |           |            |
| Diode Forward Voltage <sup>(Note 3)</sup>            | $V_{SD}$     | $V_{GS}=0V, I_S=11A$  | -   | -    | 1.2       | V          |
| Diode Forward Current <sup>(Note 2)</sup>            | $I_S$        | -   | -   | -    | 24        | A          |
| Reverse Recovery Time                                | $t_{rr}$     | $T_J = 25^\circ\text{C}, I_F = 15A$<br>$di/dt = 100A/\mu\text{s}$ <sup>(Note 3)</sup> | -   | 90   | -         | nS         |
| Reverse Recovery Charge                              | $Q_{rr}$     |   | -   | 300  | -         | nC         |
| Forward Turn-On Time                                 | $t_{on}$     | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)                  |     |      |           |            |

**Notes:**

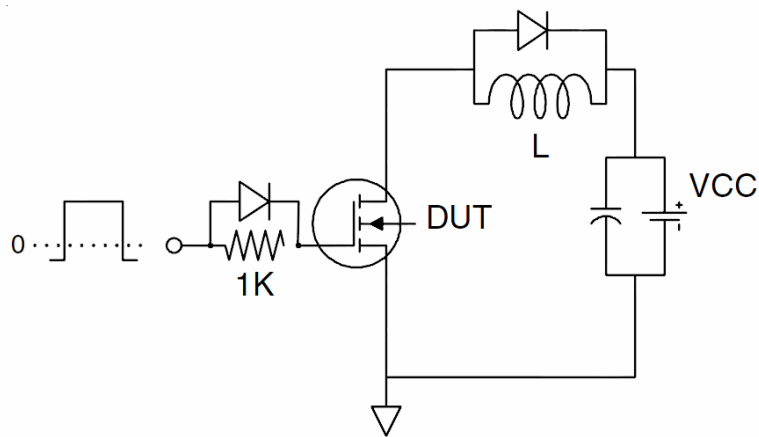
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^\circ\text{C}, V_{DD}=100V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

## Test circuit

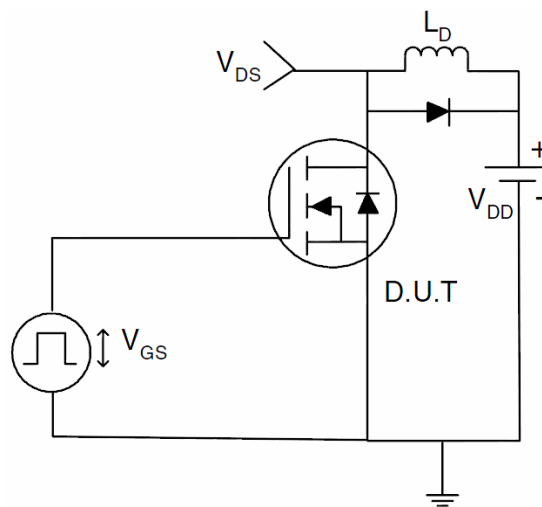
### 1) E<sub>AS</sub> test Circuit



### 2) Gate charge test Circuit



### 3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

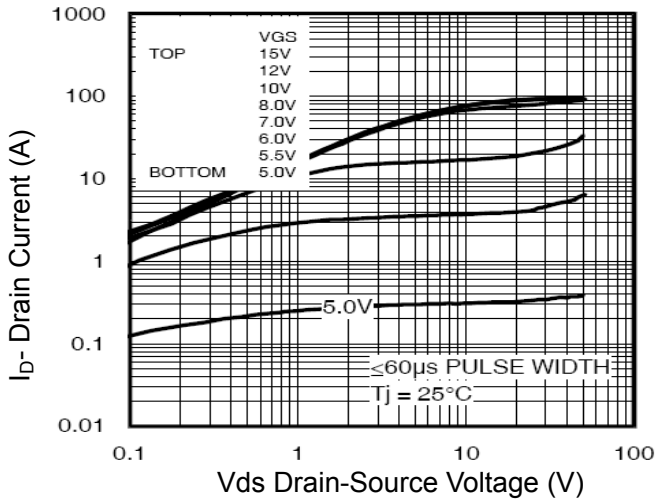


Figure 1 Output Characteristics

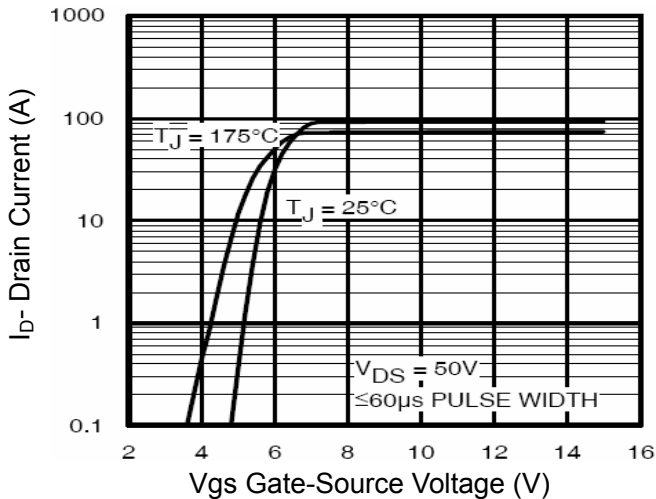


Figure 2 Transfer Characteristics

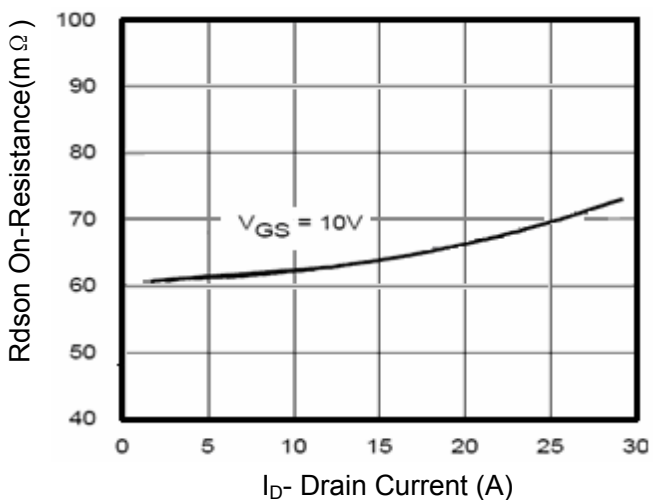


Figure 3 Rdson- Drain Current

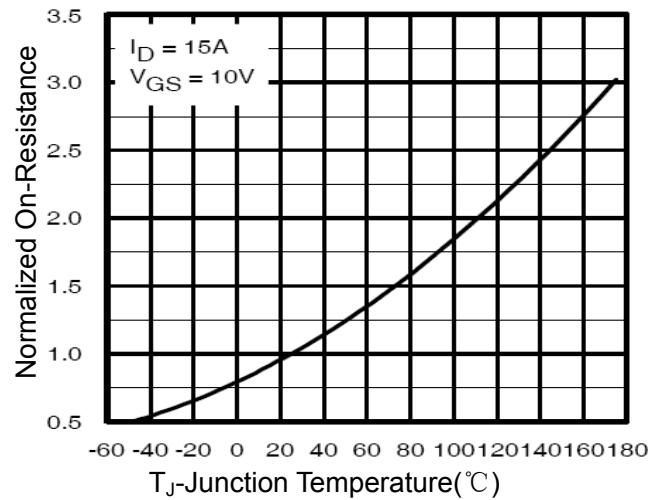


Figure 4 Rdson-Junction Temperature

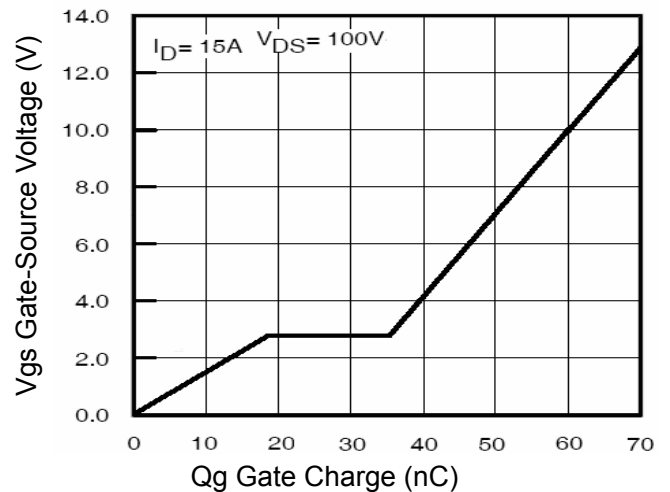


Figure 5 Gate Charge

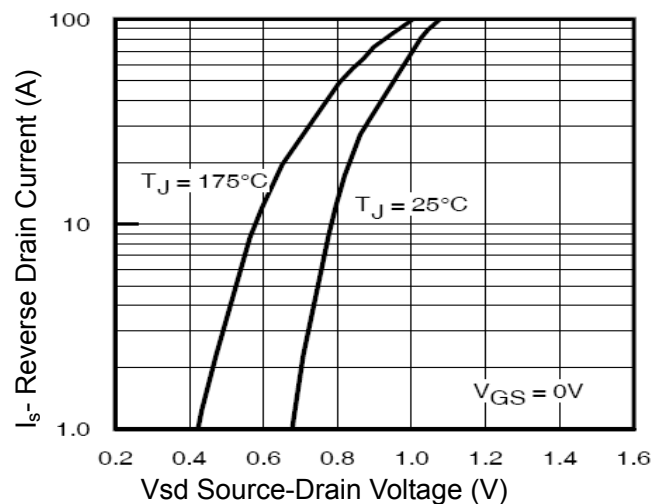


Figure 6 Source- Drain Diode Forward

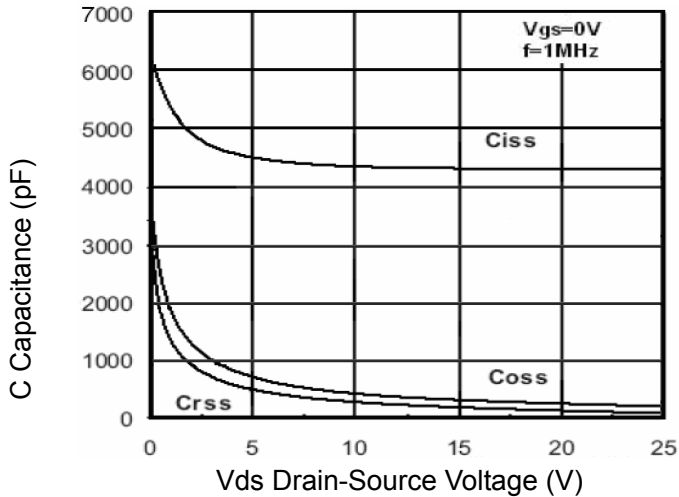


Figure 7 Capacitance vs Vds

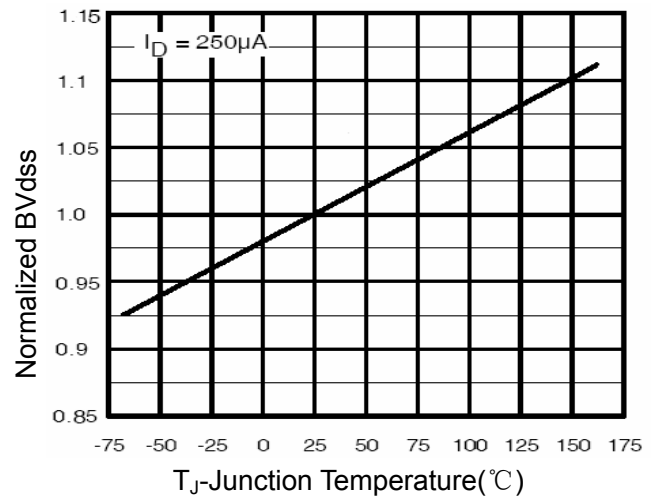


Figure 9  $BV_{DSS}$  vs Junction Temperature

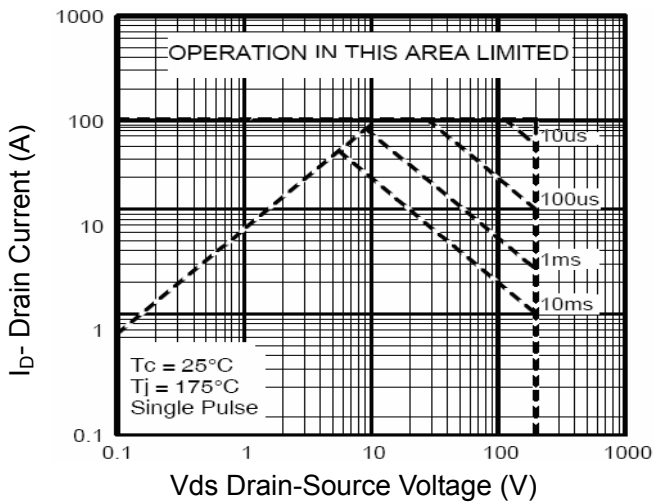


Figure 8 Safe Operation Area

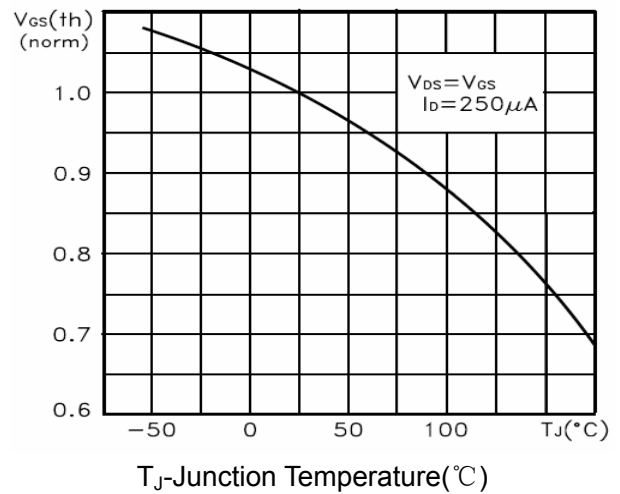


Figure 10  $V_{GS(th)}$  vs Junction Temperature

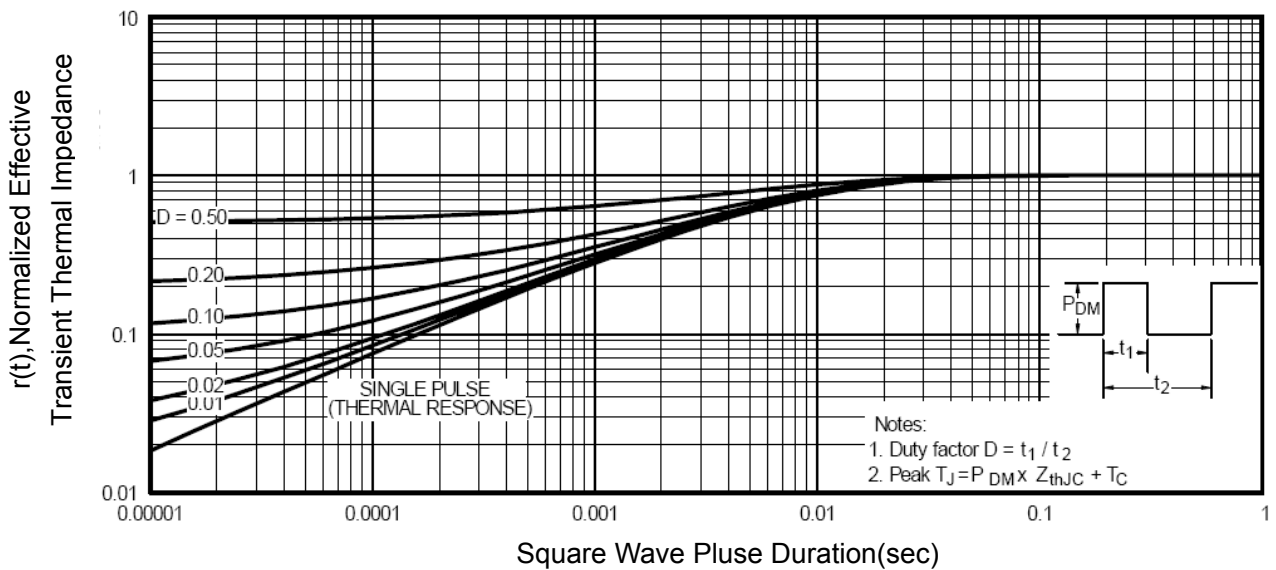
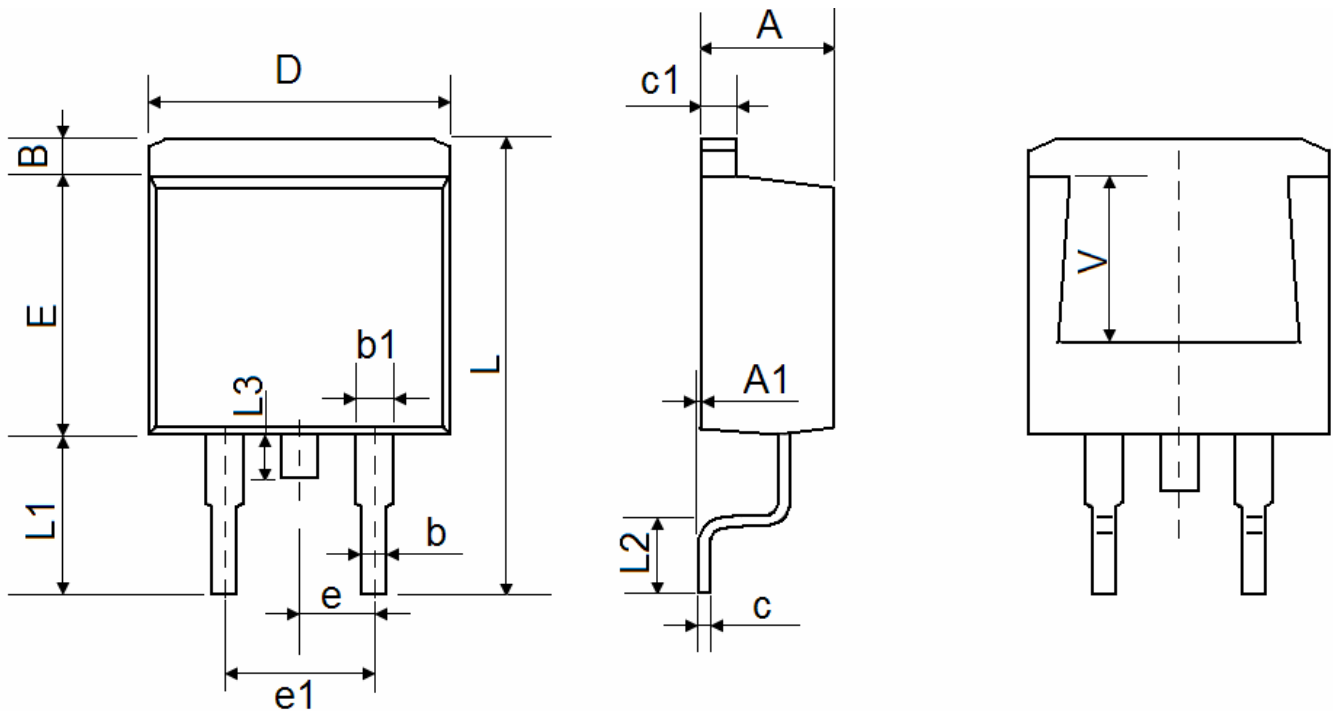


Figure 11 Normalized Maximum Transient Thermal Impedance

**TO-263-2L Package Information**


| Symbol | Dimensions In Millimeters |        | Dimensions In Inches |       |
|--------|---------------------------|--------|----------------------|-------|
|        | Min.                      | Max.   | Min.                 | Max.  |
| A      | 4.470                     | 4.670  | 0.176                | 0.184 |
| A1     | 0.000                     | 0.150  | 0.000                | 0.006 |
| B      | 1.170                     | 1.370  | 0.046                | 0.054 |
| b      | 0.710                     | 0.910  | 0.028                | 0.036 |
| b1     | 1.170                     | 1.370  | 0.046                | 0.054 |
| c      | 0.310                     | 0.530  | 0.012                | 0.021 |
| c1     | 1.170                     | 1.370  | 0.046                | 0.054 |
| D      | 10.010                    | 10.310 | 0.394                | 0.406 |
| E      | 8.500                     | 8.900  | 0.335                | 0.350 |
| e      | 2.540 TYP.                |        | 0.100 TYP.           |       |
| e1     | 4.980                     | 5.180  | 0.196                | 0.204 |
| L      | 15.050                    | 15.450 | 0.593                | 0.608 |
| L1     | 5.080                     | 5.480  | 0.200                | 0.216 |
| L2     | 2.340                     | 2.740  | 0.092                | 0.108 |
| L3     | 1.300                     | 1.700  | 0.051                | 0.067 |
| V      | 5.600 REF                 |        | 0.220 REF            |       |

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